

# NTS0304E

4-bit dual supply translating transceiver; open drain; auto direction sensing

Rev. 1.3 — 9 October 2023

Product data sheet

## 1 General description

The NTS0304E is a 4-bit, dual supply translating transceiver family with auto direction sensing, that enables bidirectional voltage level translation. It features eight 1-bit input-output ports (A and B), one output enable input (OE) and two supply pins ( $V_{CC(A)}$  and  $V_{CC(B)}$ ).  $V_{CC(A)}$  can be supplied at any voltage between 0.95 V and 3.6 V.  $V_{CC(B)}$  can be supplied at any voltage between 1.65 V and 5.5 V. This flexibility makes the device suitable for translating between any of the voltage nodes (0.95 V, 1.2 V, 1.8 V, 2.5 V, 3.3 V and 5.0 V). Pins A and OE are referenced to  $V_{CC(A)}$  and pin B is referenced to  $V_{CC(B)}$ . A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state.

## 2 Features and benefits

- Wide supply voltage range:
  - $V_{CC(A)}$ : 0.95 V to 3.6 V and  $V_{CC(B)}$ : 1.65 V to 5.5 V
- No power-sequencing required
- Maximum data rate
  - Open-drain: 2 Mbps
  - Push-pull: 20 Mbps
- Longer one-shot pulse for driving larger capacitive loads with much reduced ringing and overshoot
- A-side and OE inputs accept voltages up to 3.6 V and are 3.6 V tolerant
- B-side inputs accept voltages up to 5.5 V and are 5.5 V tolerant
- ESD protection:
  - IEC 61000-4-2 Class 4, 8 kV contact for B-side port
  - HBM JESD22-A114E Class 2 exceeds 2000 V for both ports
  - CDM JESD22-C101E exceeds 1000 V for both ports
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Package options: TSSOP14 and WLCSP12
- Specified from -40 °C to +125 °C

## 3 Applications

- I<sup>2</sup>C/SMBus, UART
- GPIO

## 4 Ordering information

Table 1. Ordering information

Type number	Topside marking	Package		
		Name	Description	Version
NTS0304EUK	S4	WLCSP12	wafer level chip scale package; 12 balls with 0.4 mm pitch; 1.42 x 1.97 x 0.525 mm	SOT1390-10



4-bit dual supply translating transceiver; open drain; auto direction sensing

Table 1. Ordering information...continued

Type number	Topside marking	Package		
		Name	Description	Version
NTS0304EPW	NTS0304	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1

4.1 Ordering options

Table 2. Ordering options

Type number	Orderable part number	Package	Packing method	Minimum order quantity	Temperature
NTS0304EUK	NTS0304EUKZ	WLCSP12	reel 7" q1/t1 *special mark chips dp	4000	T <sub>amb</sub> = -40 °C to +125 °C
NTS0304EPW	NTS0304EPWJ	TSSOP14	reel 13" q1/t1 *standard mark smd	2500	T <sub>amb</sub> = -40 °C to +125 °C

5 Functional diagram

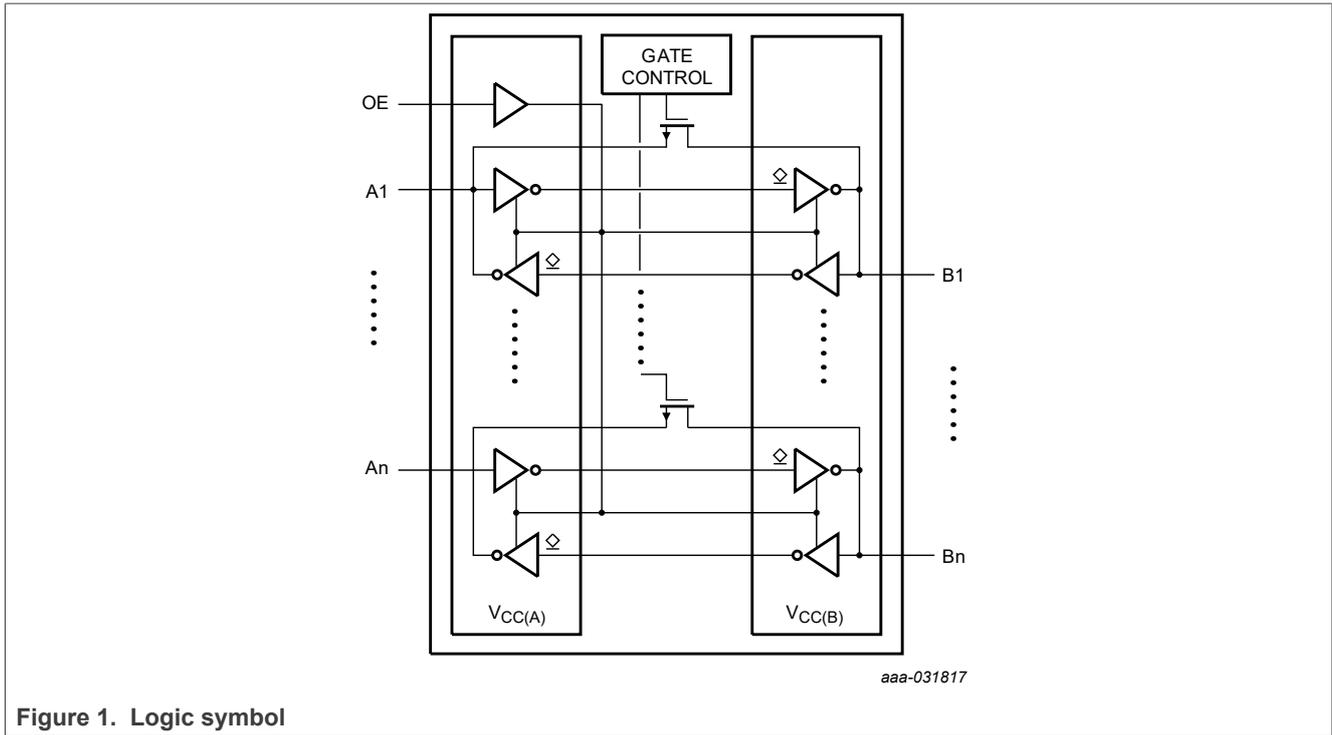


Figure 1. Logic symbol

## 6 Pinning information

### 6.1 Pinning

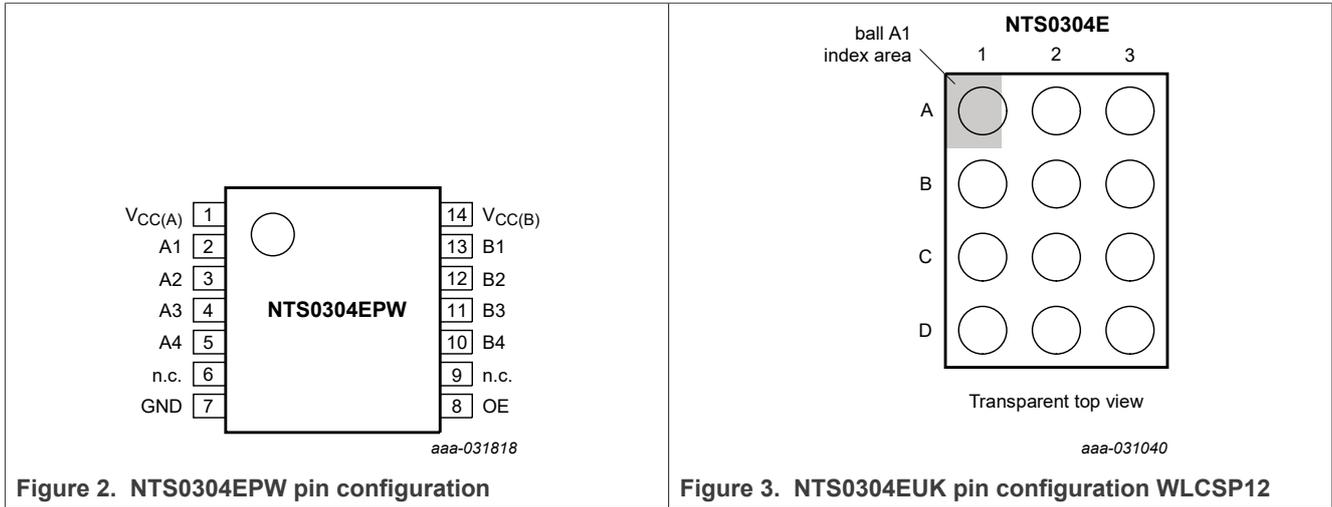


Figure 2. NTS0304EPW pin configuration

Figure 3. NTS0304EUK pin configuration WLCSP12

### 6.2 Pin description

Table 3. NTS0304E Pin description

Symbol	Pin	Ball	Description
	SOT402-1	WLCSP12	
V <sub>CC(A)</sub>	1	B2	supply voltage A
A1, A2, A3, A4	2, 3, 4, 5	A3, B3, C3, D3	data input or output (referenced to V <sub>CC(A)</sub> )
n.c.	6, 9	-	not connected
GND	7	D2	ground (0 V)
OE	8	C2	output enable input (active HIGH; referenced to V <sub>CC(A)</sub> )
B4, B3, B2, B1	10, 11, 12, 13	D1, C1, B1, A1	data input or output (referenced to V <sub>CC(B)</sub> )
V <sub>CC(B)</sub>	14	A2	supply voltage B

## 7 Functional description

Table 4. Function table<sup>[1]</sup>

Supply voltage		Input	Input/output	
V <sub>CC(A)</sub>	V <sub>CC(B)</sub>	OE	A	B
0.95 V to V <sub>CC(B)</sub>	1.65 V to 5.5 V	L	Z	Z
0.95 V to V <sub>CC(B)</sub>	1.65 V to 5.5 V	H	input or output	output or input
GND <sup>[2]</sup>	GND <sup>[2]</sup>	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either V<sub>CC(A)</sub> or V<sub>CC(B)</sub> is at GND level, the device goes into power-down mode.

## 8 Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CC(A)}$	supply voltage A			-0.5	+4.6	V
$V_{CC(B)}$	supply voltage B			-0.5	+6.5	V
$V_I$	input voltage	A port and OE input	[1][2]	-0.5	+6.5	V
		B port	[1][2]	-0.5	+6.5	V
$V_O$	output voltage	Active mode	[1][2]			
		A or B port		-0.5	$V_{CCO} + 0.5$	V
		Power-down or 3-state mode	[1]			
		A port		-0.5	+4.6	V
		B port		-0.5	+6.5	V
$I_{IK}$	input clamping current	$V_I < 0$ V		-50	-	mA
$I_{OK}$	output clamping current	$V_O < 0$ V		-50	-	mA
$I_O$	output current	$V_O = 0$ V to $V_{CCO}$	[2]	-	$\pm 50$	mA
$I_{CC}$	supply current	$I_{CC(A)}$ or $I_{CC(B)}$		-	100	mA
$I_{GND}$	ground current			-100	-	mA
$T_{stg}$	storage temperature			-65	+150	°C

[1] The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed.

[2]  $V_{CCO}$  is the supply voltage associated with the output.

## 9 Recommended operating conditions

**Table 6. Recommended operating conditions**<sup>[1][2]</sup>

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CC(A)}$	supply voltage A		[2]	0.95	3.6	V
$V_{CC(B)}$	supply voltage B			1.65	5.5	V
$V_{I\_EN}$	EN input voltage			-0.3	$V_{CC(A)} + 0.3$	V
$T_{amb}$	ambient temperature			-40	+125	°C
$T_J$	junction temperature		[3]	-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	A or B port; push-pull driving				
		$V_{CC(A)} = 0.95$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V	[2]	-	10	ns/V
		OE input				
		$V_{CC(A)} = 0.95$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V		-	10	ns/V

[1] The A and B sides of an unused I/O pair must be held in the same state, both at  $V_{CC1}$  or both at GND.

[2]  $V_{CC(A)}$  must be less than or equal to  $V_{CC(B)}$ .

[3] The  $T_J$  limits shall be supported by proper thermal PCB design taking the power consumption and the thermal resistance as listed in [Section 10](#) into account.

## 10 Thermal characteristics

Table 7. Thermal resistance information

Symbol	Rating	NTS0304EPW (TSSOP14)	NTS0304EUK (WLCSP12)
$R_{\theta JA}$	Junction to ambient	114.9	57.8
$\Psi_{JT}$	Junction to top characterization	1.6	0.2

## 11 Static characteristics

Table 8. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_I$	input leakage current	OE input; $V_I = 0\text{ V to }3.6\text{ V}$ ; $V_{CC(A)} = 0.95\text{ V to }3.6\text{ V}$ ; $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	-	$\pm 1$	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	A or B port; $V_O = 0\text{ V or }V_{CCO}$ ; $V_{CC(A)} = 0.95\text{ V to }3.6\text{ V}$ ; $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	[1]	-	$\pm 1$	$\mu\text{A}$
$C_I$	input capacitance	OE input; $V_{CC(A)} = 3.3\text{ V}$ ; $V_{CC(B)} = 3.3\text{ V}$	-	1	-	pF
$C_{I/O}$	input/output capacitance	A port	-	4	-	pF
		B port	-	7.5	-	pF
		A or B port; $V_{CC(A)} = 3.3\text{ V}$ ; $V_{CC(B)} = 3.3\text{ V}$	-	11	-	pF

[1]  $V_{CCO}$  is the supply voltage associated with the output.

Table 9. Typical supply current

At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

$V_{CC(A)}$			$V_{CC(B)}$						Unit
	1.65 V		2.5 V		3.3 V		5.0 V		
	$I_{CC(A)}$	$I_{CC(B)}$	$I_{CC(A)}$	$I_{CC(B)}$	$I_{CC(A)}$	$I_{CC(B)}$	$I_{CC(A)}$	$I_{CC(B)}$	
0.95 V	0.1	0.1	0.1	0.5	0.1	0.5	0.1	3	$\mu\text{A}$
1.2 V	0.1	0.1	0.1	0.5	0.1	0.5	0.1	3	$\mu\text{A}$
1.8 V	-	-	0.1	0.5	0.1	0.5	0.1	3	$\mu\text{A}$
2.5 V	-	-	0.2	0.5	0.1	0.5	0.1	3	$\mu\text{A}$
3.3 V	-	-	-	-	0.1	0.1	0.1	2	$\mu\text{A}$

4-bit dual supply translating transceiver; open drain; auto direction sensing

Table 10. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit	
			Min	Max	Min	Max		
V <sub>IH</sub>	HIGH-level input voltage	A port						
		V <sub>CC(A)</sub> = 0.95 V to 1.65 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V	[1]	V <sub>CCI</sub> - 0.2	-	V <sub>CCI</sub> - 0.2	-	V
		V <sub>CC(A)</sub> = 1.65 V to 3.6 V; V <sub>CC(B)</sub> = 2.3 V to 5.5 V	[1]	V <sub>CCI</sub> - 0.4	-	V <sub>CCI</sub> - 0.4	-	V
		B port						
		V <sub>CC(A)</sub> = 0.95 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V	[1]	V <sub>CCI</sub> - 0.4	-	V <sub>CCI</sub> - 0.4	-	V
		OE input						
		V <sub>CC(A)</sub> = 0.95 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		0.65V <sub>CC(A)</sub>	-	0.65V <sub>CC(A)</sub>	-	V
V <sub>IL</sub>	LOW-level input voltage	A or B port						
		V <sub>CC(A)</sub> = 0.95 V to 1.65 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	0.13	-	0.13	V
		V <sub>CC(A)</sub> = 1.65 V to 3.6 V; V <sub>CC(B)</sub> = 2.3 V to 5.5 V		-	0.15	-	0.15	V
		OE input						
		V <sub>CC(A)</sub> = 0.95 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	0.35V <sub>CC(A)</sub>	-	0.35V <sub>CC(A)</sub>	V
V <sub>OHA</sub>	HIGH-level output voltage	I <sub>O</sub> = -20 μA						
		V <sub>CC(B)</sub> = 1.65 V to 5.5 V; V <sub>CCI</sub> = V <sub>CC(B)</sub> - 0.4 V	[2]					
		V <sub>CC(A)</sub> = 1.65 V to 3.6 V	[2]	0.8V <sub>CC(A)</sub>	-	0.75V <sub>CC(A)</sub>	-	V
		V <sub>CC(A)</sub> = 0.95 V to 1.65 V	[2]	0.65V <sub>CC(A)</sub>	-	0.62V <sub>CC(A)</sub>	-	V
V <sub>OHB</sub>	HIGH-level output voltage	I <sub>O</sub> = -20 μA						
		V <sub>CC(A)</sub> = 0.95 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V; V <sub>CCI</sub> = V <sub>CC(A)</sub> - 0.2 V	[2]	0.8V <sub>CC(B)</sub>	-	0.75V <sub>CC(B)</sub>	-	V
V <sub>OL</sub>	LOW-level output voltage	A or B port; I <sub>O</sub> = 1 mA	[2]					
		V <sub>I</sub> ≤ 0.15 V; V <sub>CC(A)</sub> = 0.95 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	0.30	-	0.30	V
I <sub>I</sub>	input leakage current	OE input; V <sub>I</sub> = 0 V to 3.6 V; V <sub>CC(A)</sub> = 0.95 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	±2	-	±12	μA
I <sub>OZ</sub>	OFF-state output current	A or B port; V <sub>O</sub> = 0 V or V <sub>CCO</sub> ; V <sub>CC(A)</sub> = 0.95 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V	[2]	-	±2	-	±12	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CCI</sub> ; I <sub>O</sub> = 0 A	[1]					
		I <sub>CC(A)</sub>						

4-bit dual supply translating transceiver; open drain; auto direction sensing

Table 10. Static characteristics...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	
		$V_{CC(A)} = 0.95\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	2.4	-	15	$\mu\text{A}$
		$V_{CC(A)} = 3.6\text{ V}; V_{CC(B)} = 0\text{ V}$	-	2.2	-	15	$\mu\text{A}$
		$V_{CC(A)} = 0\text{ V}; V_{CC(B)} = 5.5\text{ V}$	-	-1	-	-8	$\mu\text{A}$
		$I_{CC(B)}$					
		$V_{CC(A)} = 0.95\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	18	-	51	$\mu\text{A}$
		$V_{CC(A)} = 3.6\text{ V}; V_{CC(B)} = 0\text{ V}$	-	-1	-	-5	$\mu\text{A}$
		$V_{CC(A)} = 0\text{ V}; V_{CC(B)} = 5.5\text{ V}$	-	18	-	46	$\mu\text{A}$
		$I_{CC(A)} + I_{CC(B)}$					
		$V_{CC(A)} = 0.95\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 1.65\text{ V to }5.5\text{ V}$	-	14.4	-	59	$\mu\text{A}$

[1]  $V_{CC1}$  is the supply voltage associated with the input.  
 [2]  $V_{CC0}$  is the supply voltage associated with the output.

12 Dynamic characteristics

Table 11. Dynamic characteristics for temperature range -40 °C to +125 °C<sup>[1]</sup>

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6; for wave forms, see Figure 4 and Figure 5.

Symbol	Parameter	Conditions	$V_{CC(B)}$						Unit
			1.8 V		3.3 V		5.0 V		
			Min	Max	Min	Max	Min	Max	
$V_{CC(A)} = 0.95\text{ V}$									
$t_{PHL}$	HIGH to LOW propagation delay	A to B	-	20	-	11.1	-	12.3	ns
$t_{PLH}$	LOW to HIGH propagation delay	A to B	-	14.8	-	12.5	-	12.2	ns
$t_{PHL}$	HIGH to LOW propagation delay	B to A	-	9.2	-	5.2	-	5.2	ns
$t_{PLH}$	LOW to HIGH propagation delay	B to A	-	8.8	-	2.9	-	1.4	ns
$t_{en}$	enable time	OE to A; B	-	200	-	200	-	200	ns
$t_{dis}$	disable time	OE to A; no external load <sup>[2]</sup>	-	100	-	100	-	100	ns
		OE to B; no external load <sup>[2]</sup>	-	100	-	100	-	100	ns
		OE to A	-	250	-	250	-	250	ns
		OE to B	-	220	-	220	-	220	ns
$t_{TLH}$	LOW to HIGH output transition time	A port	6.0	15.3	2.2	15.1	1.8	11.1	ns
		B port	6.0	17.0	4.0	14.0	4.0	20.0	ns

4-bit dual supply translating transceiver; open drain; auto direction sensing

Table 11. Dynamic characteristics for temperature range -40 °C to +125 °C<sup>[1]</sup>...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6; for wave forms, see Figure 4 and Figure 5.

Symbol	Parameter	Conditions	V <sub>CC(B)</sub>						Unit	
			1.8 V		3.3 V		5.0 V			
			Min	Max	Min	Max	Min	Max		
t <sub>THL</sub>	HIGH to LOW output transition time	A port	0.9	18.0	0.7	9.0	0.6	9.0	ns	
		B port	1.6	22.0	2.8	10.7	3.2	14.2	ns	
t <sub>W</sub>	pulse width	data inputs	49	-	49	-	49	-	ns	
f <sub>data</sub>	data rate		[3]	-	20	-	20	-	20	Mbps

[1] t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PHZ</sub>; t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>.  
 [2] Delay between OE going LOW and when the outputs are disabled.  
 [3] Assuming a maximum one-shot accelerator pulse length of 50ns and equal time for 1 and 0 bit information

Table 12. Dynamic characteristics for temperature range -40 °C to +125 °C<sup>[1]</sup>

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6; for wave forms, see Figure 4 and Figure 5.

Symbol	Parameter	Conditions	V <sub>CC(B)</sub>						Unit	
			2.5 V		3.3 V		5.0 V			
			Min	Max	Min	Max	Min	Max		
V <sub>CC(A)</sub> = 1.8 V										
t <sub>PHL</sub>	HIGH to LOW propagation delay	A to B	-	5.8	-	5.9	-	7.3	ns	
t <sub>PLH</sub>	LOW to HIGH propagation delay	A to B	-	8.5	-	8.5	-	8.8	ns	
t <sub>PHL</sub>	HIGH to LOW propagation delay	B to A	-	5.5	-	5.7	-	5.9	ns	
t <sub>PLH</sub>	LOW to HIGH propagation delay	B to A	-	6.7	-	5.7	-	1.4	ns	
t <sub>en</sub>	enable time	OE to A; B	-	200	-	200	-	200	ns	
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	-	100	-	100	-	100	ns
		OE to B; no external load	[2]	-	100	-	100	-	100	ns
		OE to A		-	250	-	250	-	250	ns
		OE to B		-	220	-	220	-	220	ns
t <sub>TLH</sub>	LOW to HIGH output transition time	A port	3.2	11.9	1.2	11.7	1.1	9.5	ns	
		B port	3.3	13.5	2.7	14.5	2.7	13.5	ns	
t <sub>THL</sub>	HIGH to LOW output transition time	A port	1.2	7.4	1.0	7.5	1.0	16.7	ns	
		B port	2.6	9.5	2.2	9.4	2.8	12.5	ns	
t <sub>W</sub>	pulse width	data inputs	49	-	49	-	49	-	ns	
f <sub>data</sub>	data rate		[3]	-	20	-	20	-	20	Mbps
V <sub>CC(A)</sub> = 2.5 V										

4-bit dual supply translating transceiver; open drain; auto direction sensing

Table 12. Dynamic characteristics for temperature range -40 °C to +125 °C<sup>[1]</sup>...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6; for wave forms, see Figure 4 and Figure 5.

Symbol	Parameter	Conditions	V <sub>CC(B)</sub>						Unit
			2.5 V		3.3 V		5.0 V		
			Min	Max	Min	Max	Min	Max	
t <sub>PHL</sub>	HIGH to LOW propagation delay	A to B	-	4.0	-	4.2	-	4.3	ns
t <sub>PLH</sub>	LOW to HIGH propagation delay	A to B	-	4.4	-	5.2	-	5.5	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	B to A	-	3.8	-	4.5	-	5.4	ns
t <sub>PLH</sub>	LOW to HIGH propagation delay	B to A	-	3.2	-	2.0	-	1.5	ns
t <sub>en</sub>	enable time	OE to A; B	-	200	-	200	-	200	ns
t <sub>dis</sub>	disable time	OE to A; no external load <sup>[2]</sup>	-	100	-	100	-	100	ns
		OE to B; no external load <sup>[2]</sup>	-	100	-	100	-	100	ns
		OE to A	-	220	-	220	-	220	ns
		OE to B	-	220	-	220	-	220	ns
t <sub>TLH</sub>	LOW to HIGH output transition time	A port	2.8	10	1.4	8.3	1.2	7.8	ns
		B port	3.2	10.4	2.9	15.5	2.4	16.9	ns
t <sub>THL</sub>	HIGH to LOW output transition time	A port	1.0	7.2	1.0	6.9	1.0	6.7	ns
		B port	2.2	9.8	2.4	8.4	2.6	8.3	ns
t <sub>W</sub>	pulse width	data inputs	49	-	49	-	49	-	ns
f <sub>data</sub>	data rate		<sup>[3]</sup>	20	-	20	-	20	Mbps
V <sub>CC(A)</sub> = 3.3 V									
t <sub>PHL</sub>	HIGH to LOW propagation delay	A to B	-	-	-	3.0	-	3.9	ns
t <sub>PLH</sub>	LOW to HIGH propagation delay	A to B	-	-	-	5.3	-	5.5	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	B to A	-	-	-	3.2	-	4.2	ns
t <sub>PLH</sub>	LOW to HIGH propagation delay	B to A	-	-	-	3.2	-	3.3	ns
t <sub>en</sub>	enable time	OE to A; B	-	-	-	200	-	200	ns
t <sub>dis</sub>	disable time	OE to A; no external load <sup>[2]</sup>	-	-	-	100	-	100	ns
		OE to B; no external load <sup>[2]</sup>	-	-	-	100	-	100	ns
		OE to A	-	-	-	280	-	280	ns
		OE to B	-	-	-	220	-	220	ns
t <sub>TLH</sub>	LOW to HIGH output transition time	A port	-	-	1.2	13.1	1.1	7.4	ns
		B port	-	-	2.5	14.2	2.1	16.0	ns

4-bit dual supply translating transceiver; open drain; auto direction sensing

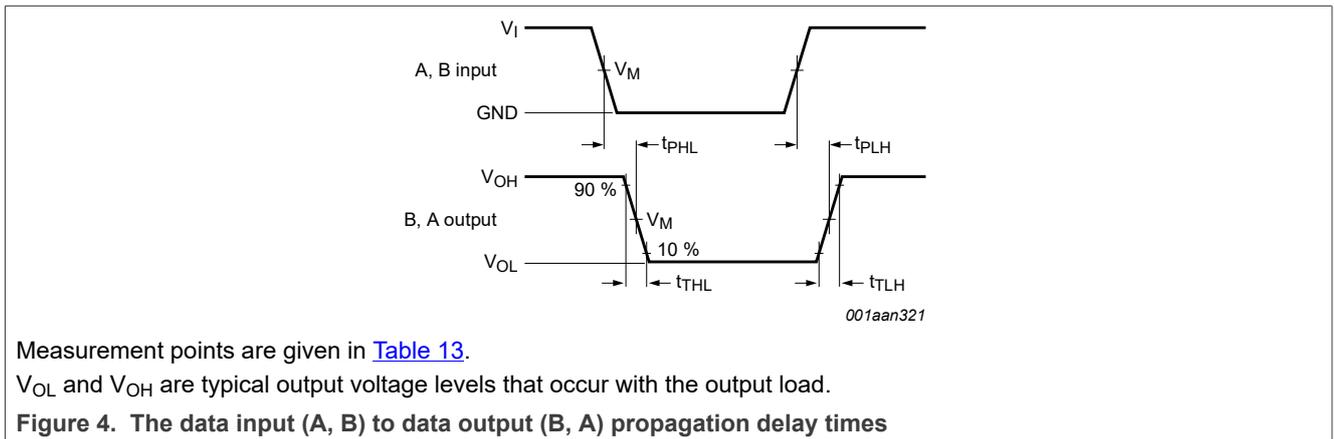
Table 12. Dynamic characteristics for temperature range -40 °C to +125 °C<sup>[1]</sup>...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6; for wave forms, see Figure 4 and Figure 5.

Symbol	Parameter	Conditions	V <sub>CC(B)</sub>						Unit	
			2.5 V		3.3 V		5.0 V			
			Min	Max	Min	Max	Min	Max		
t <sub>THL</sub>	HIGH to LOW output transition time	A port	-	-	1.0	6.8	1.0	6.3	ns	
		B port	-	-	2.3	9.3	2.4	9.5	ns	
t <sub>W</sub>	pulse width	data inputs	-	-	49	-	49	-	ns	
f <sub>data</sub>	data rate		[3]	-	-	-	20	-	20	Mbps

[1] t<sub>en</sub> is the same as t<sub>pZL</sub> and t<sub>pZH</sub>; t<sub>dis</sub> is the same as t<sub>pLZ</sub> and t<sub>pHZ</sub>.  
 [2] Delay between OE going LOW and when the outputs are disabled.  
 [3] Assuming a maximum one-shot accelerator pulse length of 50ns and equal time for 1 and 0 bit information

13 Waveforms



4-bit dual supply translating transceiver; open drain; auto direction sensing

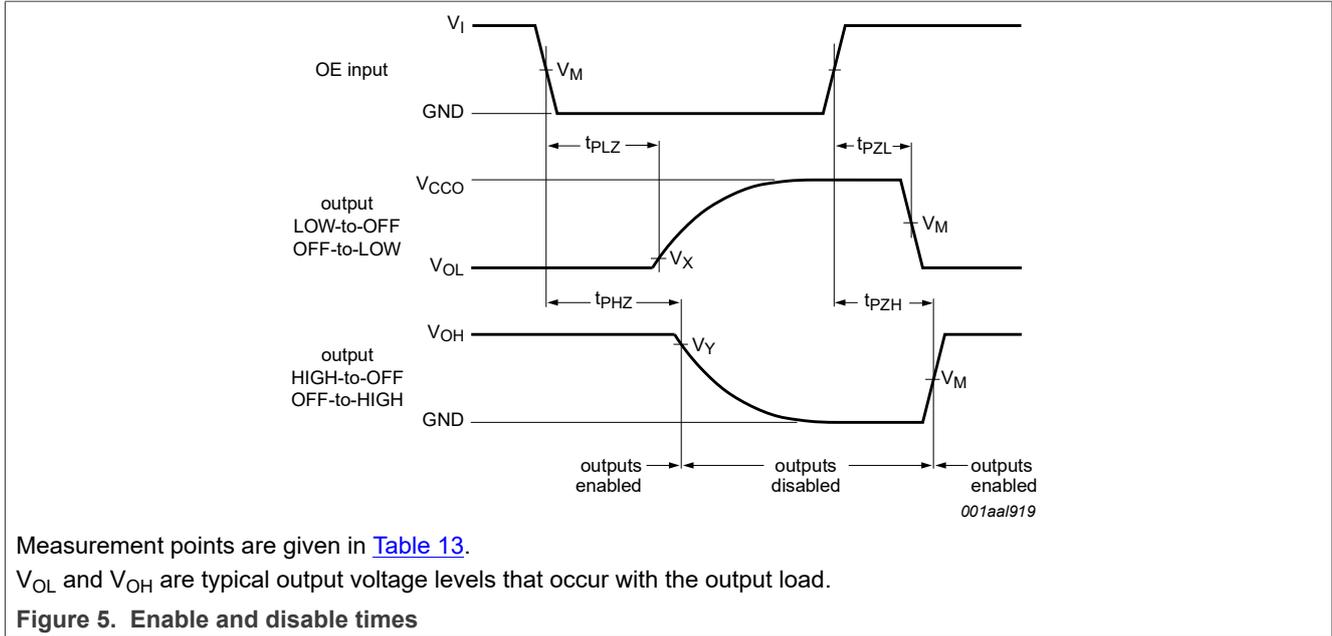


Table 13. Measurement points<sup>[1][2]</sup>

Supply voltage	Input	Output		
$V_{CCO}$	$V_M$	$V_M$	$V_X$	$V_Y$
0.95 V	$0.5V_{CCI}$	$0.5V_{CCO}$	$V_{OL} + 0.1 V$	$V_{OH} - 0.1 V$
$1.8 V \pm 0.15 V$	$0.5V_{CCI}$	$0.5V_{CCO}$	$V_{OL} + 0.15 V$	$V_{OH} - 0.15 V$
$2.5 V \pm 0.2 V$	$0.5V_{CCI}$	$0.5V_{CCO}$	$V_{OL} + 0.15 V$	$V_{OH} - 0.15 V$
$3.3 V \pm 0.3 V$	$0.5V_{CCI}$	$0.5V_{CCO}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
$5.0 V \pm 0.5 V$	$0.5V_{CCI}$	$0.5V_{CCO}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$

[1]  $V_{CCI}$  is the supply voltage associated with the input.  
 [2]  $V_{CCO}$  is the supply voltage associated with the output.

4-bit dual supply translating transceiver; open drain; auto direction sensing

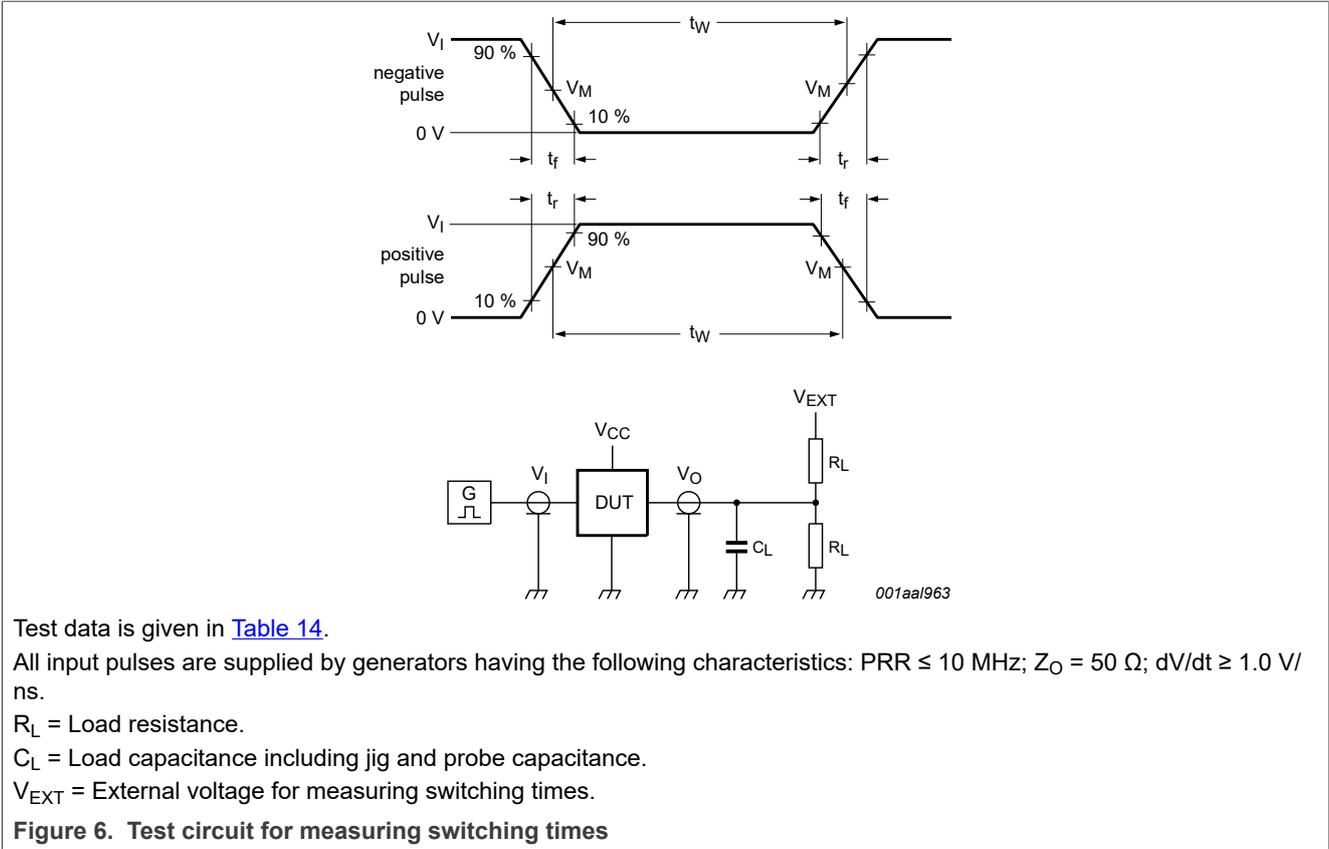


Table 14. Test data

Supply voltage		Input		Load		V <sub>EXT</sub>		
V <sub>CC(A)</sub>	V <sub>CC(B)</sub>	V <sub>I</sub> <sup>[1]</sup>	Δt/ΔV	C <sub>L</sub>	R <sub>L</sub> <sup>[2]</sup>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub> <sup>[3]</sup>
0.95 V to 3.6 V	1.65 V to 5.5 V	V <sub>CCI</sub>	≤ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V <sub>CCO</sub>

[1] V<sub>CCI</sub> is the supply voltage associated with the input.  
 [2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, R<sub>L</sub> = 1 MΩ. For measuring enable and disable times, R<sub>L</sub> = 50 kΩ.  
 [3] V<sub>CCO</sub> is the supply voltage associated with the output.

## 14 Application information

### 14.1 Applications

Voltage level-translation applications. The NTS0304E can be used in point-to-point applications to interface between devices or systems operating at different supply voltages. The device is primarily targeted at I<sup>2</sup>C or 4-wire which use open-drain drivers. It may also be used in applications where push-pull drivers are connected to the ports, however the NTB010x series of devices are more suitable.

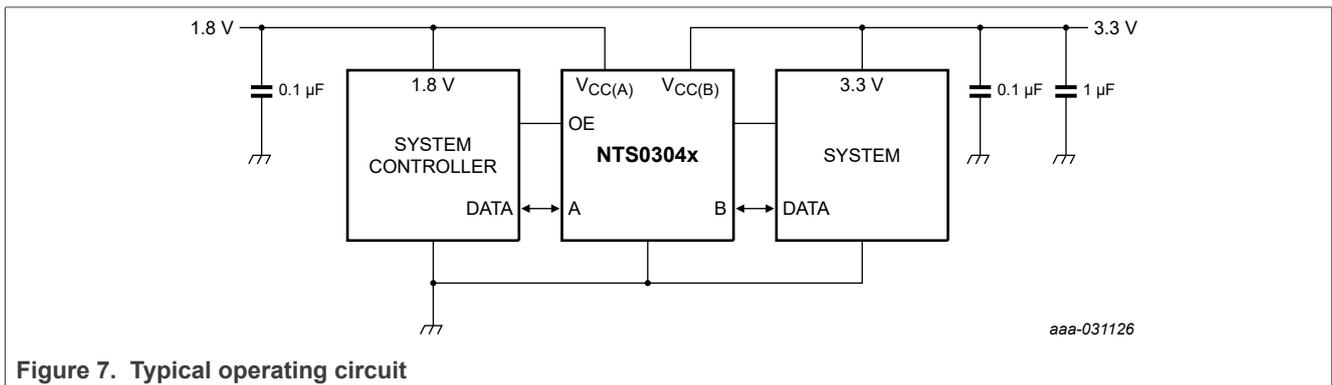


Figure 7. Typical operating circuit

### 14.2 Architecture

The architecture of the NTS0304E is shown in Figure 8. The device does not require an extra input signal to control the direction of data flow from A to B or B to A.

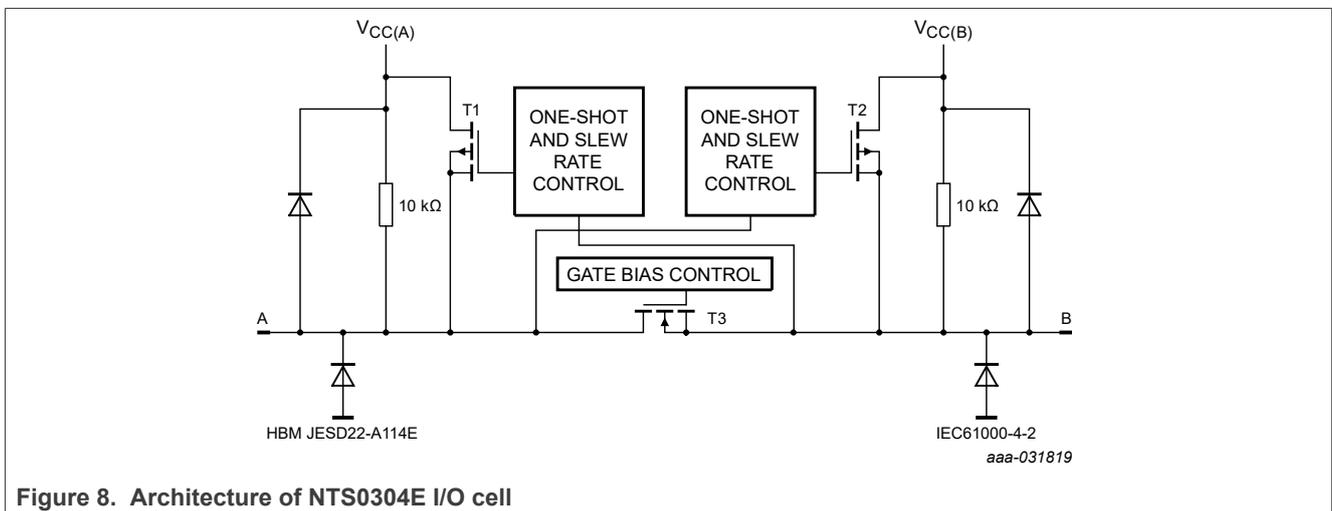


Figure 8. Architecture of NTS0304E I/O cell

The NTS0304E is a "switch" type voltage translator using two key circuits to enable voltage translation:

1. A pass-gate transistor (N-channel) that ties the ports together.
2. An output edge-rate accelerator that detects and accelerates rising edges on the I/O pins.

The gate bias voltage of the pass gate transistor (T3) is set at approximately one threshold voltage above the V<sub>CC</sub> level of the low-voltage side. During a LOW-to-HIGH transition, the output one-shot accelerates the output transition by switching on the PMOS transistors (T1, T2). It bypasses the 10 kΩ pull-up resistors and increases the current drive capability. The one-shot is activated once the input transition reaches approximately V<sub>CC1</sub>/2; it is deactivated approximately 50 ns after the output reaches V<sub>CC0</sub>/2. During the acceleration time, the driver

output resistance is between approximately 50  $\Omega$  and 70  $\Omega$ . To avoid signal contention and minimize dynamic  $I_{CC}$ , the user should wait for the one-shot circuit to turn-off before applying a signal in the opposite direction. Pull-up resistors are included in the device for DC current sourcing capability.

### 14.3 Input driver requirements

As the NTS0304E is a switch type translator, properties of the input driver directly affect the output signal. The external open-drain or push-pull driver applied to an I/O determines the static current sinking capability of the system. The max data rate, HIGH-to-LOW output transition time ( $t_{THL}$ ), and propagation delay ( $t_{PHL}$ ), are dependent upon the output impedance and edge-rate of the external driver. The limits provided for these parameters in the data sheet assume a driver with output impedance below 50  $\Omega$  is used.

### 14.4 Output load considerations

The maximum lumped capacitive load that can be driven is dependent upon the one-shot pulse duration. In cases with very heavy capacitive loading, there is a risk that the output does not reach the positive rail within the one-shot pulse duration. The NTS0304E has a longer one-shot pulse for driving larger capacitive loads.

To avoid excessive capacitive loading and to ensure correct triggering of the one-shot, use short trace lengths and low capacitance connectors on NTS0304E PCB layouts. The length of the PCB trace should be such that the round-trip delay of any reflection is within the one-shot pulse duration (approximately 50 ns). It ensures low impedance termination and avoids output signal oscillations and one-shot retriggering.

### 14.5 Output single shot slew rate control

Integrated slew-rate control and timed increase of the one-shot driver output current reduce EMI. An additional comparator circuit on the  $V_{OUT}$  side starts to reduce the one-shot driver current when  $V_{OUT} > 0.65V_{OUT}$  with a slight delay, so it can safely drive the output voltage to a safe high-level while at the same time reducing the driver strength early enough to reduce overshoots and ringing.

### 14.6 Power-up

During operation,  $V_{CC(A)}$  must never be higher than  $V_{CC(B)}$ . However, during power-up,  $V_{CC(A)} \geq V_{CC(B)}$  does not damage the device, so either power supply can be ramped up first. There is no special power-up sequencing required. The NTS0304E includes circuitry that disables all output ports when either  $V_{CC(A)}$  or  $V_{CC(B)}$  is switched off.

### 14.7 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time ( $t_{dis}$  with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time ( $t_{en}$ ) indicates the amount of time the user must allow for one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND through a pull-down resistor. The current-sourcing capability of the driver determines the minimum value of the resistor.

### 14.8 Pull-up or pull-down resistors on I/Os lines

The A port I/O has an internal 10 k $\Omega$  pull-up resistor to  $V_{CC(A)}$ . The B port I/O has an internal 10 k $\Omega$  pull-up resistor to  $V_{CC(B)}$ . If a smaller value of pull-up resistor is required, add an external resistor in parallel to the internal 10 k $\Omega$ . This pull-up resistor affects the  $V_{OL}$  level. When OE goes LOW, the internal pull-ups of the NTS0304E are disabled.

## 14.9 ESD protection on I/Os lines

The NTS0304E contains rail to rail ESD protection structures connecting the A and B I/O to their respective supply. As a consequence, if a supply pin is pulled LOW, the related I/Os are pulled low too through the upper ESD protection diode and the 10 k $\Omega$  pull-up resistor. Additionally, besides the normal HBM and CDM ESD protection features on both A and B Port I/O the B Port I/O features integrated ESD protection to IEC 61000-4-2 Class 4 system ESD level of 8kV contact for when users plug cameras, games, and other items into their USB or video ports in real-world ESD stress applications.

15 Package outline

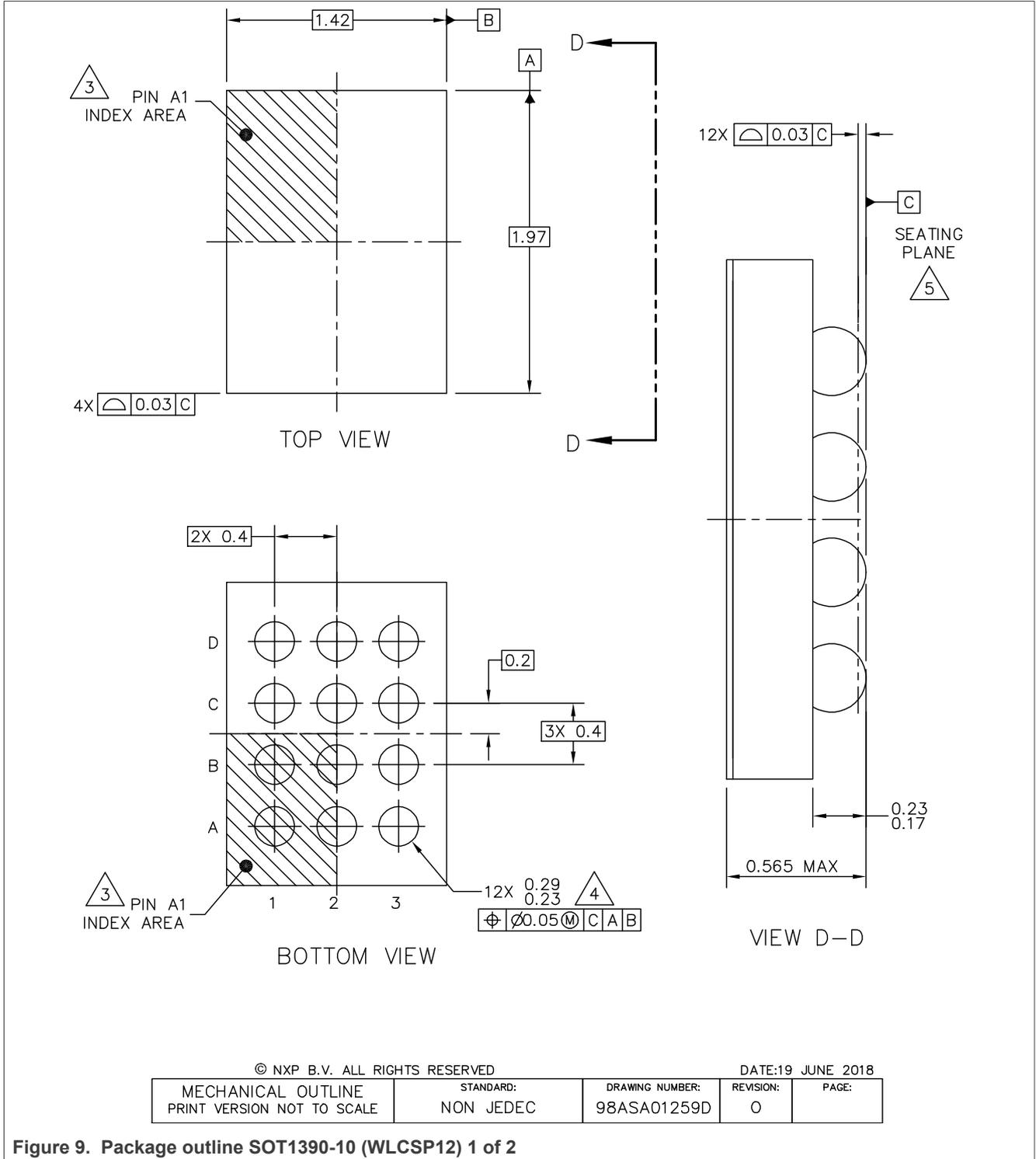


Figure 9. Package outline SOT1390-10 (WLCSP12) 1 of 2

NOTES:

1. ALL DIMENSIONS IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PIN A1 FEATURE SHAPE, SIZE AND LOCATION MAY VARY.
4. MAXIMUM SOLDER BALL DIAMETER MEASURED PARALLEL TO DATUM C.
5. DATUM C, THE SEATING PLANE, IS DETERMINED BY THE SPHERICAL CROWNS OF THE SOLDER BALL
6. THIS PACKAGE HAS A BACK SIDE COATING THICKNESS OF 0.025.

© NXP B.V. ALL RIGHTS RESERVED

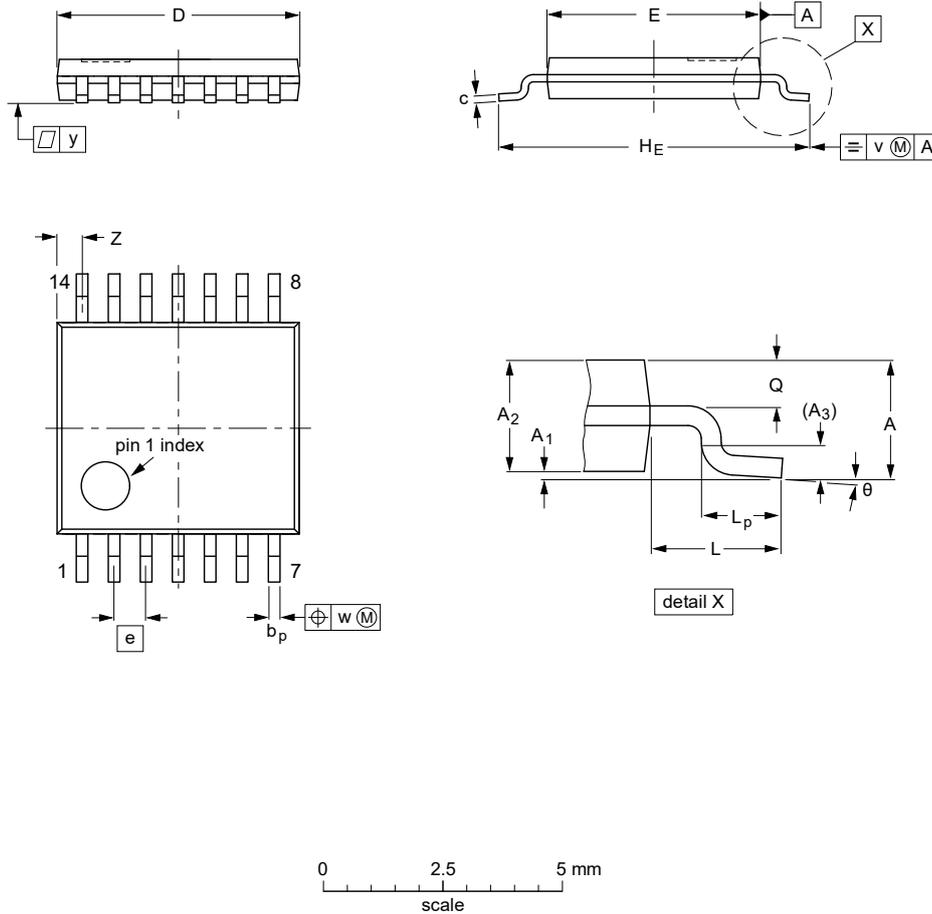
DATE:19 JUNE 2018

MECHANICAL OUTLINE PRINT VERSION NOT TO SCALE	STANDARD: NON JEDEC	DRAWING NUMBER: 98ASA01259D	REVISION: 0	PAGE:
--	------------------------	--------------------------------	----------------	-------

Figure 10. Package outline SOT1390-10 (WLCSP12) 2 of 2

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



**DIMENSIONS (mm are the original dimensions)**

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(2)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

**Notes**

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT402-1		MO-153				99-12-27 03-02-18

Figure 11. NTS0304E Package outline SOT402-1 (TSSOP14)

16 Soldering

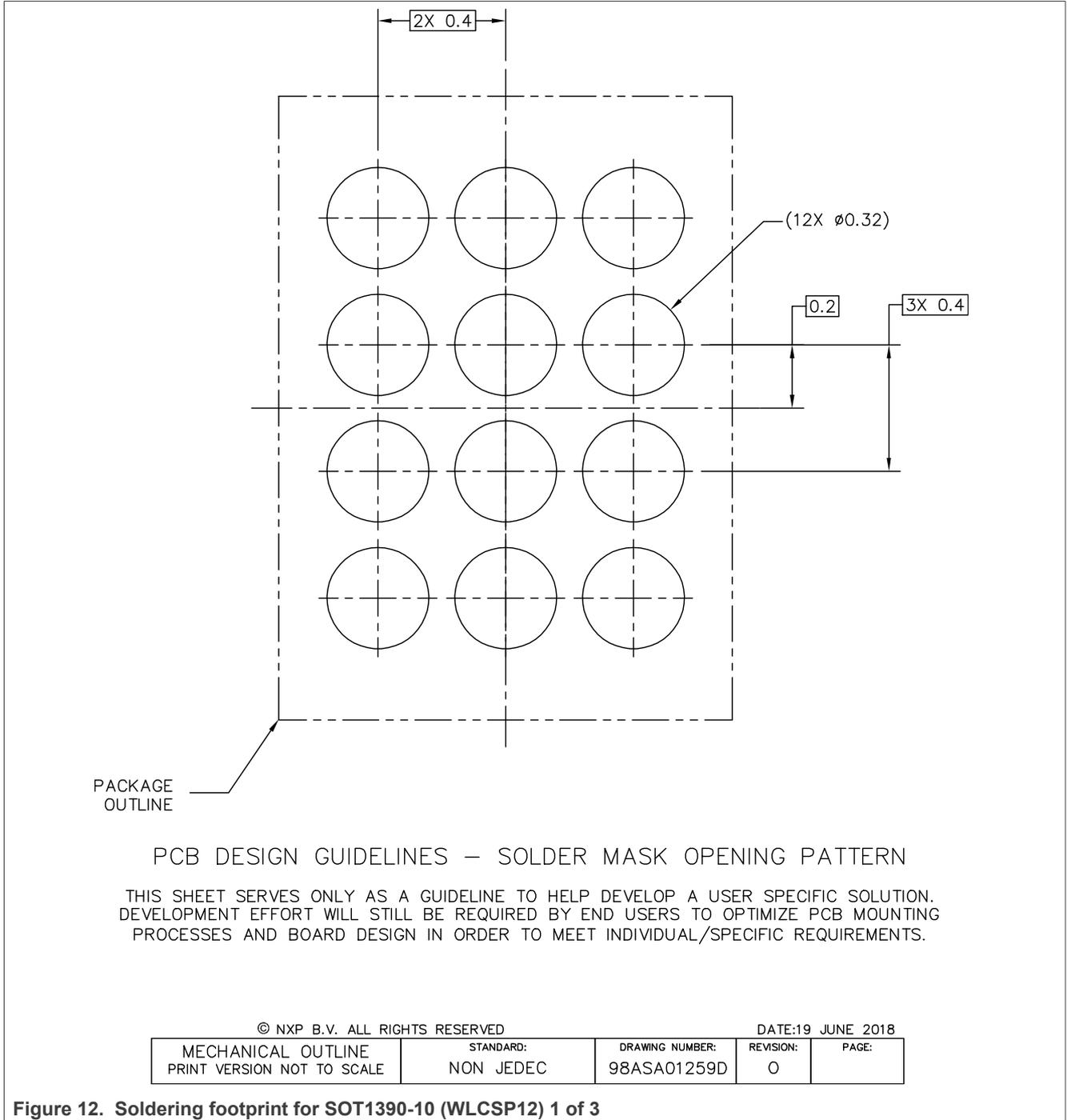


Figure 12. Soldering footprint for SOT1390-10 (WLCSP12) 1 of 3

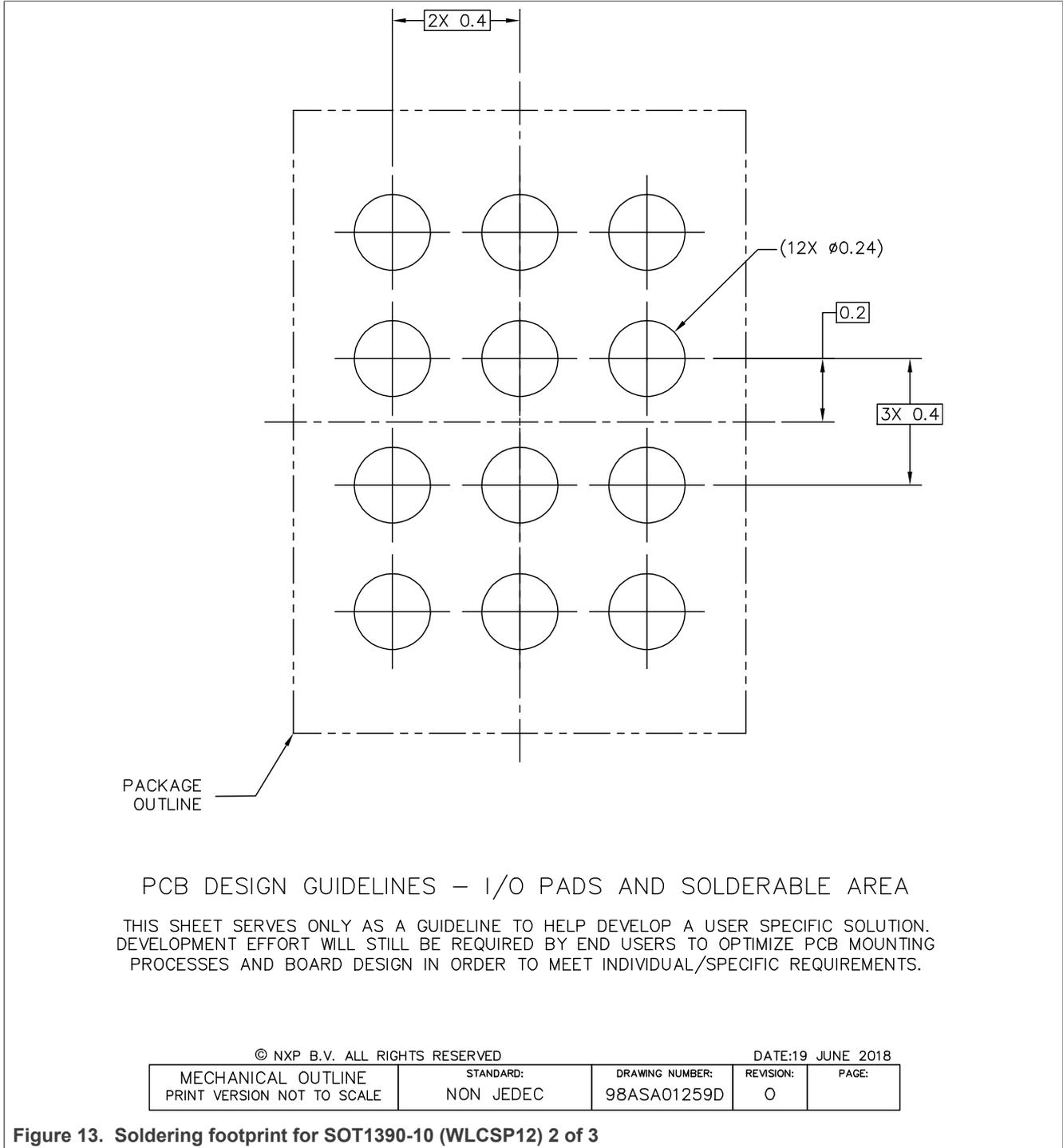


Figure 13. Soldering footprint for SOT1390-10 (WLCSP12) 2 of 3

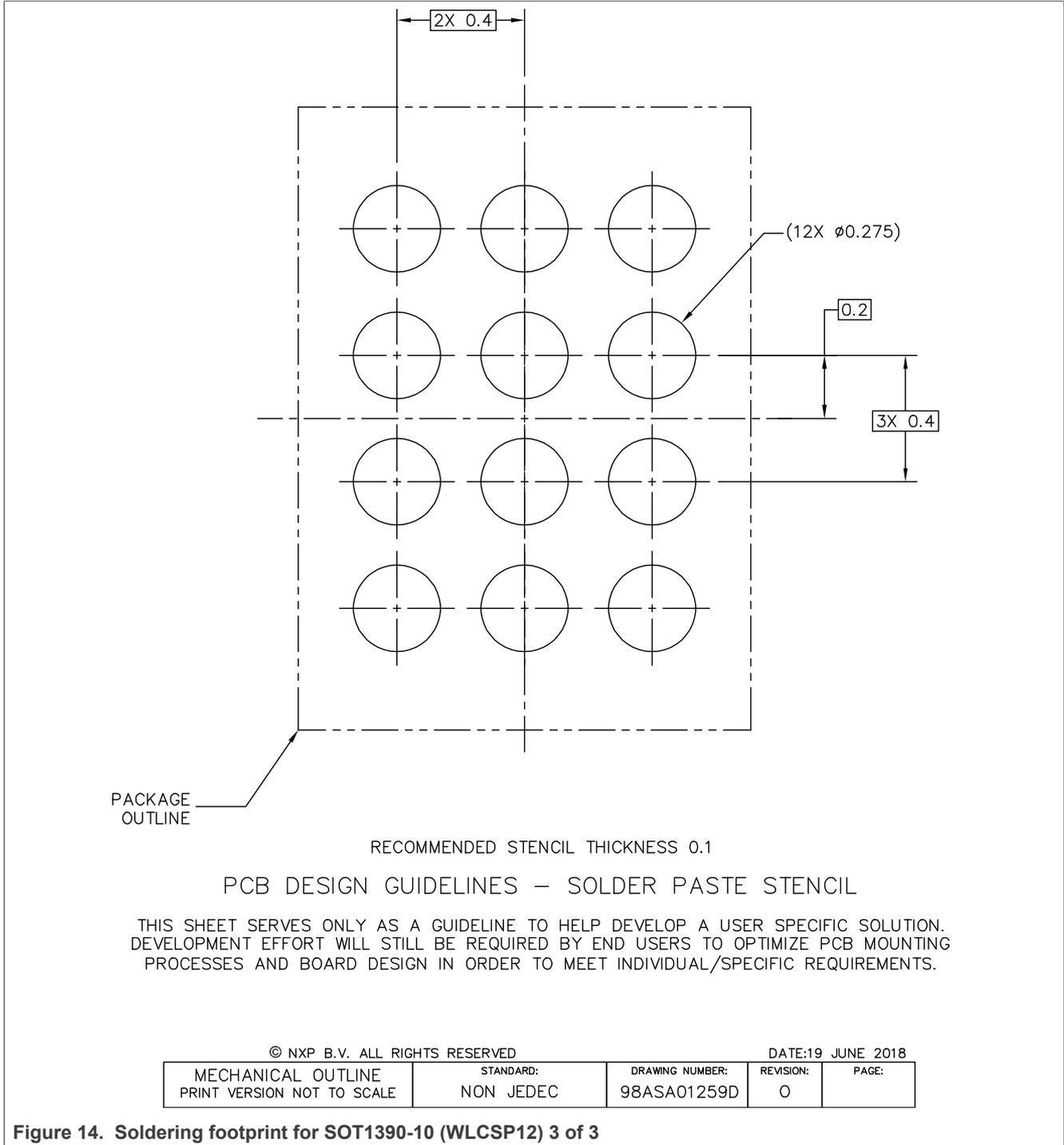


Figure 14. Soldering footprint for SOT1390-10 (WLCSP12) 3 of 3

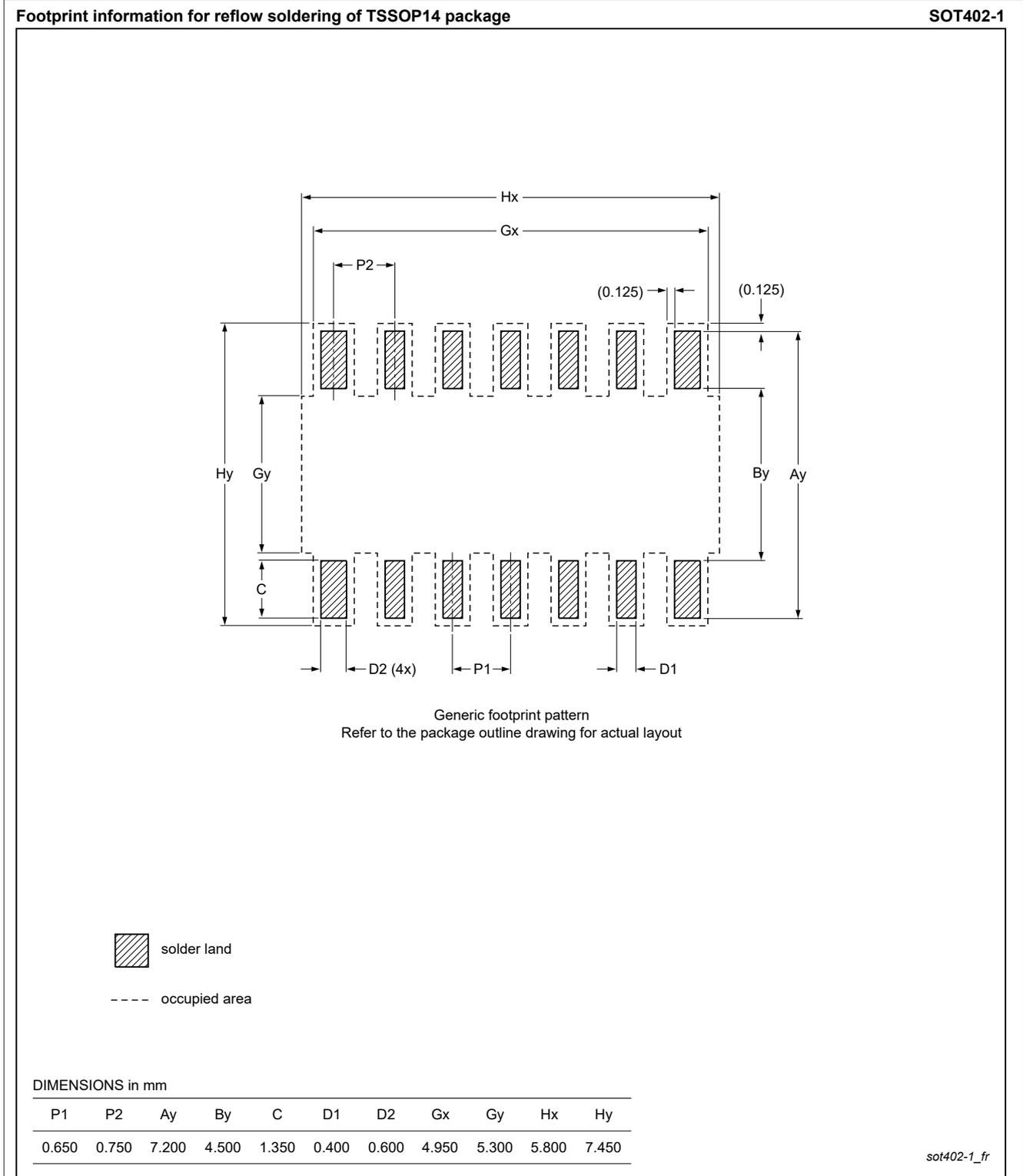


Figure 15. Soldering footprint for SOT402-1 (TSSOP14)

## 17 Abbreviations

Table 15. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
GPIO	General Purpose Input Output
HBM	Human Body Model
I <sup>2</sup> C	Inter-Integrated Circuit
IEC	International Electrotechnical Commission
MM	Machine Model
PCB	Printed-Circuit Board
PMOS	Positive Metal Oxide Semiconductor
SMBus	System Management Bus
UART	Universal Asynchronous Receiver Transmitter

## 18 Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NTS0304E v.1.3	20231009	Product data sheet	-	NTS0304E v1.2
Modifications:	<ul style="list-style-type: none"> <li>• <a href="#">Table 10</a>: Removed "0 V or" from I<sub>CC</sub> V<sub>I</sub> conditions</li> <li>• <a href="#">Section 14.1</a>: Removed text "or the newer lower voltage NTB030x..." from last sentence</li> </ul>			
NTS0304E v.1.2	20220921	Product data sheet	-	NTS0304E v1.1
NTS0304E v.1.1	20210413	Product data sheet	202103008I	NTS0304E v1.0
NTS0304E v.1.0	20190201	Product data sheet	-	-

## 19 Legal information

### 19.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 19.2 Definitions

**Draft** — A draft status on a document indicates that the content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included in a draft version of a document and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

### 19.3 Disclaimers

**Limited warranty and liability** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the Terms and conditions of commercial sale of NXP Semiconductors.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

**Terms and conditions of commercial sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

## 4-bit dual supply translating transceiver; open drain; auto direction sensing

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Suitability for use in non-automotive qualified products** — Unless this document expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

**Translations** — A non-English (translated) version of a document, including the legal information in that document, is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

**Security** — Customer understands that all NXP products may be subject to unidentified vulnerabilities or may support established security standards or specifications with known limitations. Customer is responsible for the design and operation of its applications and products throughout their lifecycles to reduce the effect of these vulnerabilities on customer's applications and products. Customer's responsibility also extends to other open and/or proprietary technologies supported by NXP products for use in customer's applications. NXP accepts no liability for any vulnerability. Customer should regularly check security updates from NXP and follow up appropriately.

Customer shall select products with security features that best meet rules, regulations, and standards of the intended application and make the ultimate design decisions regarding its products and is solely responsible for compliance with all legal, regulatory, and security related requirements concerning its products, regardless of any information or support that may be provided by NXP.

NXP has a Product Security Incident Response Team (PSIRT) (reachable at [PSIRT@nxp.com](mailto:PSIRT@nxp.com)) that manages the investigation, reporting, and solution release to security vulnerabilities of NXP products.

**NXP B.V.** - NXP B.V. is not an operating company and it does not distribute or sell products.

## 19.4 Trademarks

Notice: All referenced brands, product names, service names, and trademarks are the property of their respective owners.

**NXP** — wordmark and logo are trademarks of NXP B.V.

Tables

Tab. 1.	Ordering information	1	Tab. 10.	Static characteristics	6
Tab. 2.	Ordering options	2	Tab. 11.	Dynamic characteristics for temperature range -40 °C to +125 °C	7
Tab. 3.	NTS0304E Pin description	3	Tab. 12.	Dynamic characteristics for temperature range -40 °C to +125 °C	8
Tab. 4.	Function table	3	Tab. 13.	Measurement points	11
Tab. 5.	Limiting values	4	Tab. 14.	Test data	12
Tab. 6.	Recommended operating conditions	4	Tab. 15.	Abbreviations	23
Tab. 7.	Thermal resistance information	5	Tab. 16.	Revision history	23
Tab. 8.	Typical static characteristics	5			
Tab. 9.	Typical supply current	5			

Figures

Fig. 1.	Logic symbol	2	Fig. 10.	Package outline SOT1390-10 (WLCSP12) 2 of 2	17
Fig. 2.	NTS0304EPW pin configuration	3	Fig. 11.	NTS0304E Package outline SOT402-1 (TSSOP14)	18
Fig. 3.	NTS0304EUK pin configuration WLCSP12	3	Fig. 12.	Soldering footprint for SOT1390-10 (WLCSP12) 1 of 3	19
Fig. 4.	The data input (A, B) to data output (B, A) propagation delay times	10	Fig. 13.	Soldering footprint for SOT1390-10 (WLCSP12) 2 of 3	20
Fig. 5.	Enable and disable times	11	Fig. 14.	Soldering footprint for SOT1390-10 (WLCSP12) 3 of 3	21
Fig. 6.	Test circuit for measuring switching times	12	Fig. 15.	Soldering footprint for SOT402-1 (TSSOP14)	22
Fig. 7.	Typical operating circuit	13			
Fig. 8.	Architecture of NTS0304E I/O cell	13			
Fig. 9.	Package outline SOT1390-10 (WLCSP12) 1 of 2	16			

---

## Contents

---

<b>1</b>	<b>General description</b> .....	<b>1</b>
<b>2</b>	<b>Features and benefits</b> .....	<b>1</b>
<b>3</b>	<b>Applications</b> .....	<b>1</b>
<b>4</b>	<b>Ordering information</b> .....	<b>1</b>
4.1	Ordering options .....	2
<b>5</b>	<b>Functional diagram</b> .....	<b>2</b>
<b>6</b>	<b>Pinning information</b> .....	<b>3</b>
6.1	Pinning .....	3
6.2	Pin description .....	3
<b>7</b>	<b>Functional description</b> .....	<b>3</b>
<b>8</b>	<b>Limiting values</b> .....	<b>4</b>
<b>9</b>	<b>Recommended operating conditions</b> .....	<b>4</b>
<b>10</b>	<b>Thermal characteristics</b> .....	<b>5</b>
<b>11</b>	<b>Static characteristics</b> .....	<b>5</b>
<b>12</b>	<b>Dynamic characteristics</b> .....	<b>7</b>
<b>13</b>	<b>Waveforms</b> .....	<b>10</b>
<b>14</b>	<b>Application information</b> .....	<b>13</b>
14.1	Applications .....	13
14.2	Architecture .....	13
14.3	Input driver requirements .....	14
14.4	Output load considerations .....	14
14.5	Output single shot slew rate control .....	14
14.6	Power-up .....	14
14.7	Enable and disable .....	14
14.8	Pull-up or pull-down resistors on I/Os lines .....	14
14.9	ESD protection on I/Os lines .....	15
<b>15</b>	<b>Package outline</b> .....	<b>16</b>
<b>16</b>	<b>Soldering</b> .....	<b>19</b>
<b>17</b>	<b>Abbreviations</b> .....	<b>23</b>
<b>18</b>	<b>Revision history</b> .....	<b>23</b>
<b>19</b>	<b>Legal information</b> .....	<b>24</b>

---

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

---